

# MOSFET - Power, Single N-Channel, SO-8 FL

30 V, 3.4 mΩ, 71 A

NVMFS4C306N

## Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- AEC-Q101 Qualified and PPAP Capable
- NVMFS4C306NWF – Wettable Flanks Option for Enhanced Optical Inspection
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## Applications

- Reverse Battery Protection
- DC-DC Converters Output Driver

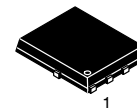
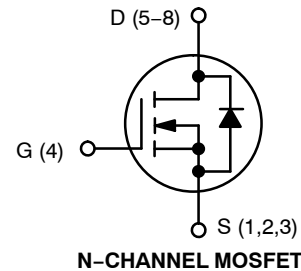
## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	30	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	$I_D$	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	$P_D$	3	W
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	$I_D$	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	$I_D$	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)	$P_D$	36.5	W
Pulsed Drain Current	$I_{DM}$	166	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	28	A
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $V_{GS} = 10\text{ V}$ , $I_L = 37\text{ A}_{pk}$ , $L = 0.1\text{ mH}$ , $R_{GS} = 25\text{ }\Omega$ ) (Note 3)	$E_{AS}$	68	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

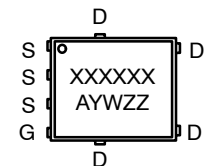
1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.
3. Parts are 100% tested at  $T_J = 25^\circ\text{C}$ ,  $V_{GS} = 10\text{ V}$ ,  $I_L = 27\text{ A}_{pk}$ ,  $E_{AS} = 36\text{ mJ}$ .

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
30 V	3.4 mΩ @ 10 V	71 A
	4.8 mΩ @ 4.5 V	



SO-8 FLAT LEAD  
CASE 488AA  
STYLE 1

## MARKING DIAGRAM



4C06N = Specific Device Code for NVMFS4C306N

4C06WF = Specific Device Code for NVMFS4C306NWF

A = Assembly Location

Y = Year

W = Work Week

ZZ = Lot Traceability

## ORDERING INFORMATION

Device	Package	Shipping†
NVMFS4C306NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel

## DISCONTINUED (Note 1)

NVMFS4C306NWF1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on [www.onsemi.com](http://www.onsemi.com).

# NVMFS4C306N

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	4.1	°C/W
Junction-to-Ambient – Steady State	$R_{\theta JA}$	49	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage (transient)	$V_{(BR)DSSst}$	$V_{GS} = 0\text{ V}, I_{D(aval)} = 12.6\text{ A}, T_{case} = 25^\circ\text{C}, t_{transient} = 100\text{ ns}$	34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			14.4		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.3		2.1	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			3.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		2.8	3.4	m $\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		4.0	4.8	
Forward Transconductance	$g_{FS}$	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		58		S
Gate Resistance	$R_G$	$T_A = 25^\circ\text{C}$	0.3	1.0	2.0	$\Omega$

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		1683		pF
Output Capacitance	$C_{OSS}$			841		
Reverse Transfer Capacitance	$C_{RSS}$			40		
Capacitance Ratio	$C_{RSS}/C_{ISS}$	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}, f = 1\text{ MHz}$		0.023		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		11.6		nC
Threshold Gate Charge	$Q_{G(TH)}$			2.6		
Gate-to-Source Charge	$Q_{GS}$			4.7		
Gate-to-Drain Charge	$Q_{GD}$			4.0		
Gate Plateau Voltage	$V_{GP}$			3.1		V
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		26		nC

### SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		10		ns
Rise Time	$t_r$			32		
Turn-Off Delay Time	$t_{d(OFF)}$			18		
Fall Time	$t_f$			5.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		8.0		ns
Rise Time	$t_r$			28		
Turn-Off Delay Time	$t_{d(OFF)}$			24		
Fall Time	$t_f$			3.0		

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

# NVMFS4C306N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 10\text{ A}$	$T_J = 25^\circ\text{C}$	0.8	1.1	V
			$T_J = 125^\circ\text{C}$	0.63		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$		34		ns
Charge Time	$t_a$			17		
Discharge Time	$t_b$			17		
Reverse Recovery Charge	$Q_{RR}$			22		nC

- Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

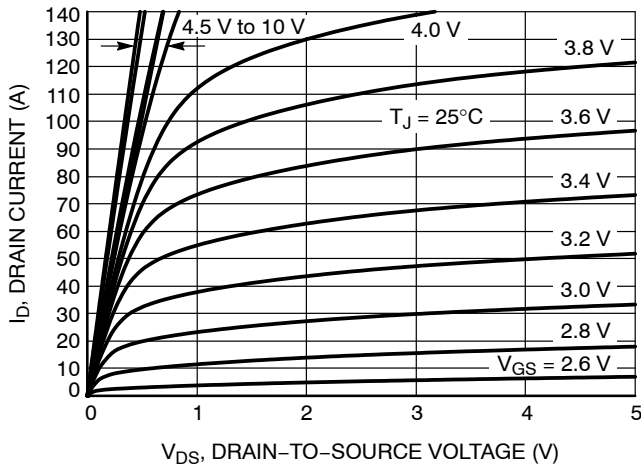


Figure 1. On-Region Characteristics

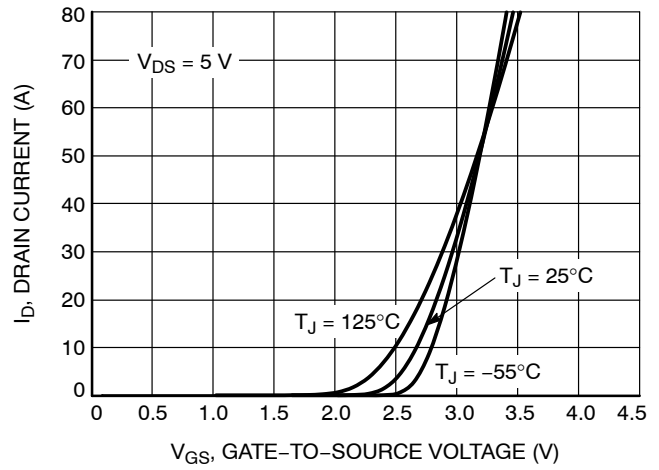


Figure 2. Transfer Characteristics

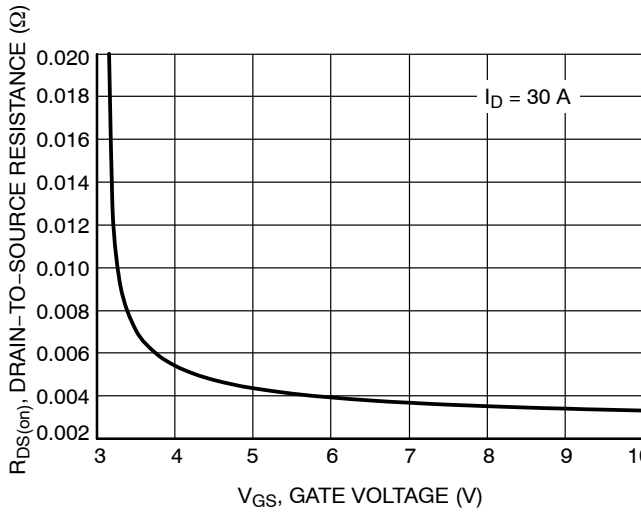


Figure 3. On-Resistance vs. Gate-to-Source Voltage

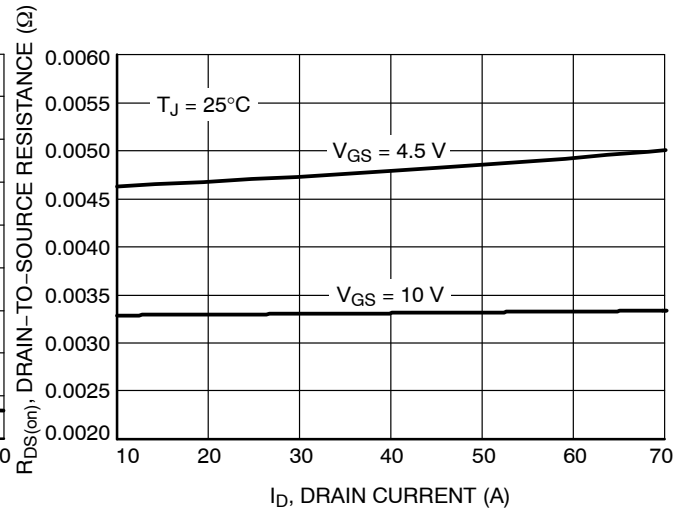


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

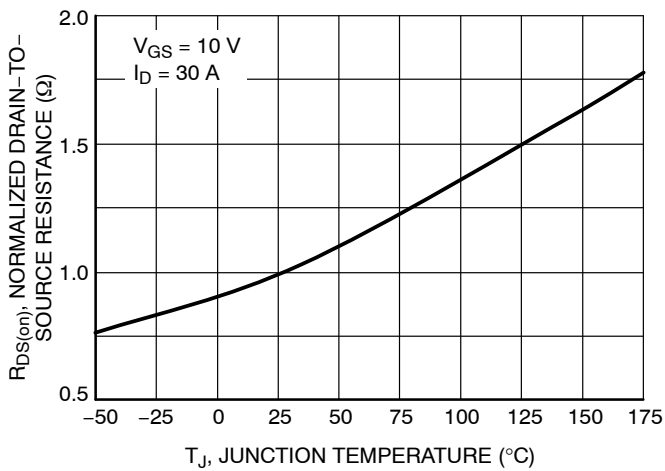


Figure 5. On-Resistance Variation with Temperature

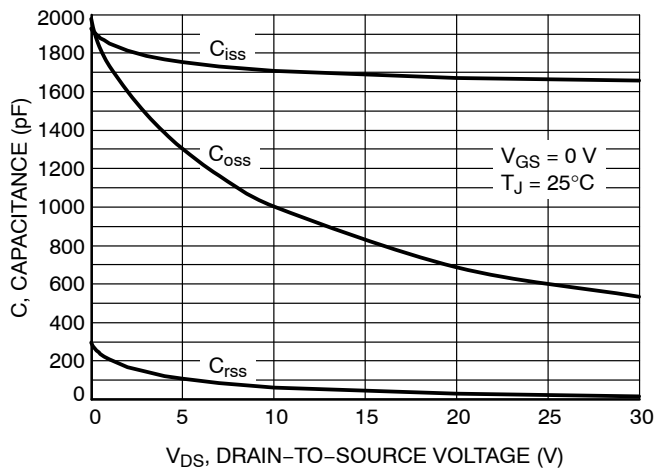


Figure 6. Capacitance Variation

TYPICAL CHARACTERISTICS

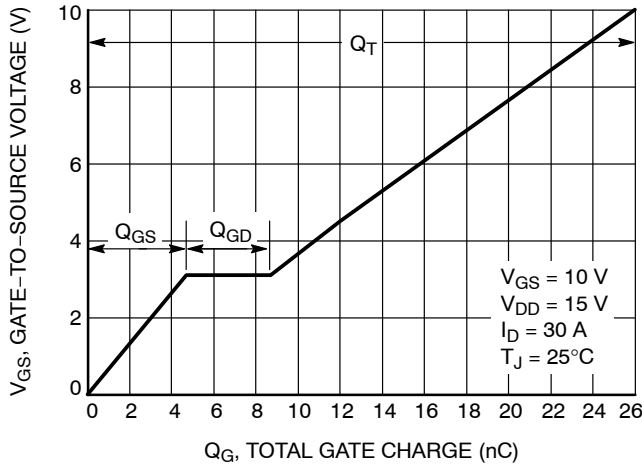


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

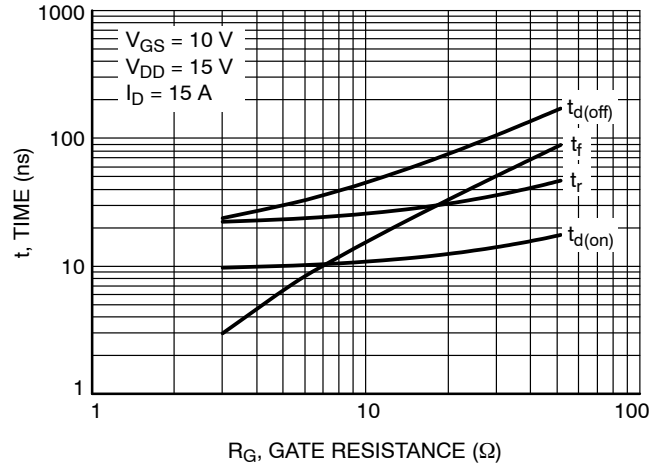


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

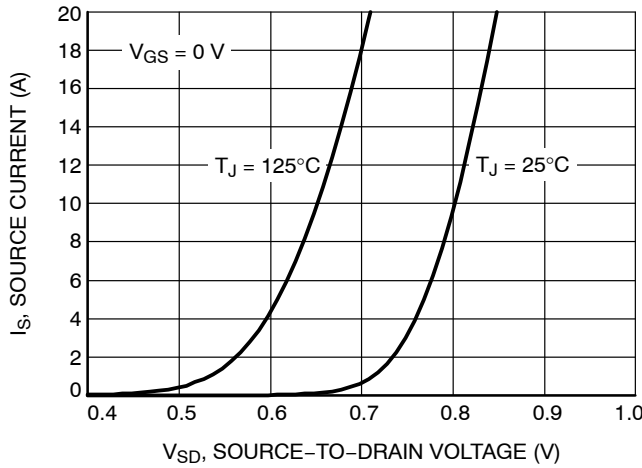


Figure 9. Diode Forward Voltage vs. Current

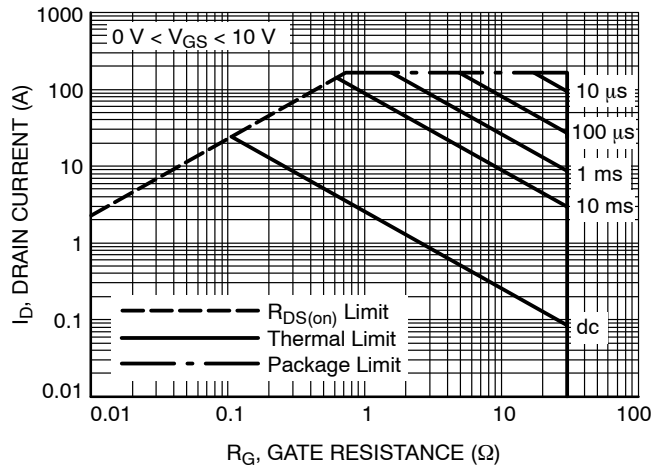


Figure 10. Maximum Rated Forward Biased Safe Operating Area

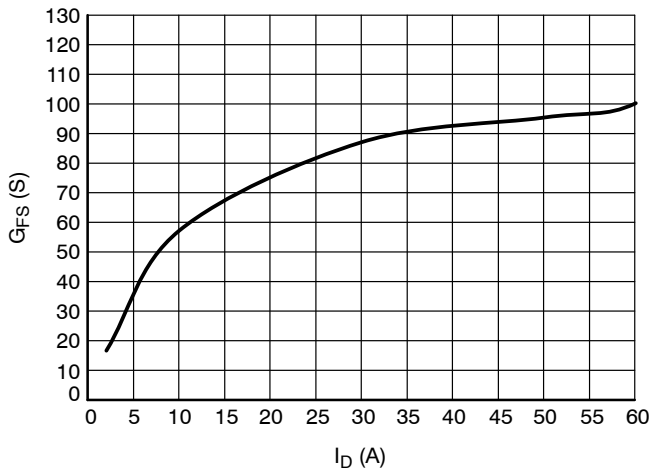


Figure 11.  $G_{FS}$  vs.  $I_D$

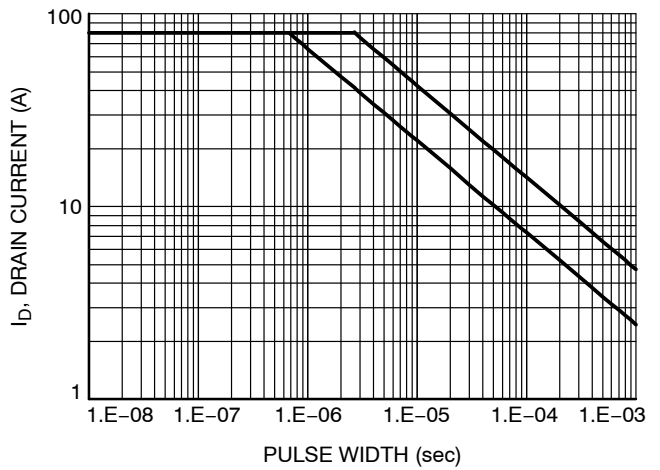


Figure 12. Avalanche Characteristics

# NVMFS4C306N

## TYPICAL CHARACTERISTICS

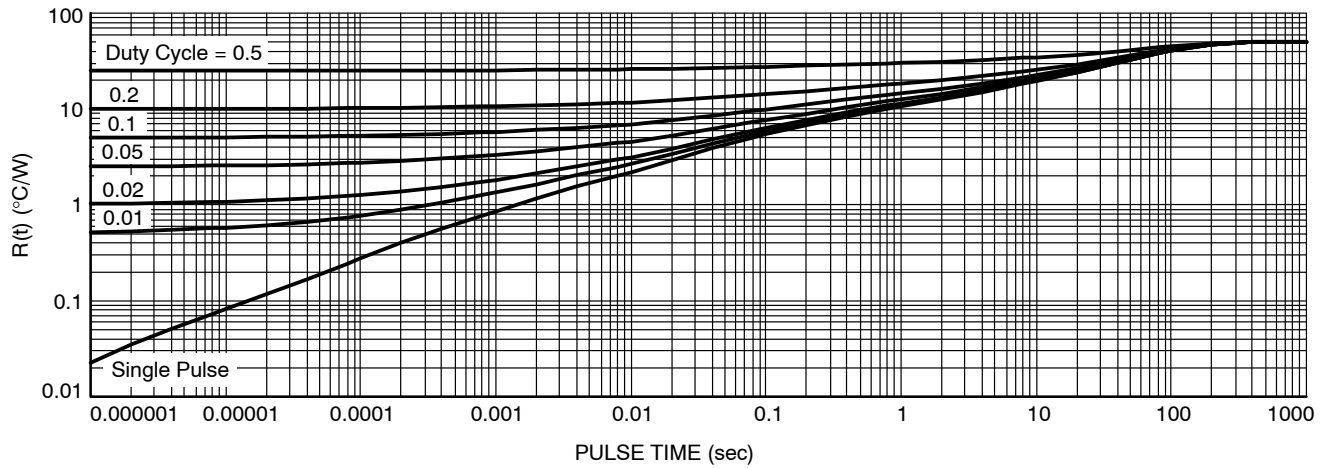


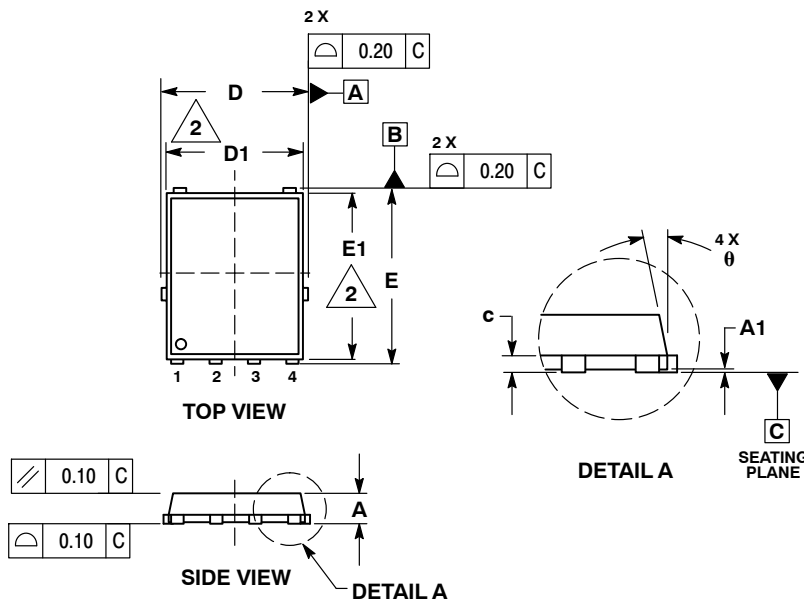
Figure 13. Thermal Response



SCALE 2:1

**DFN5 5x6, 1.27P**  
**(SO-8FL)**  
**CASE 488AA**  
**ISSUE N**

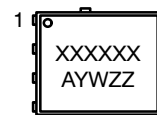
DATE 25 JUN 2018



## NOTES:

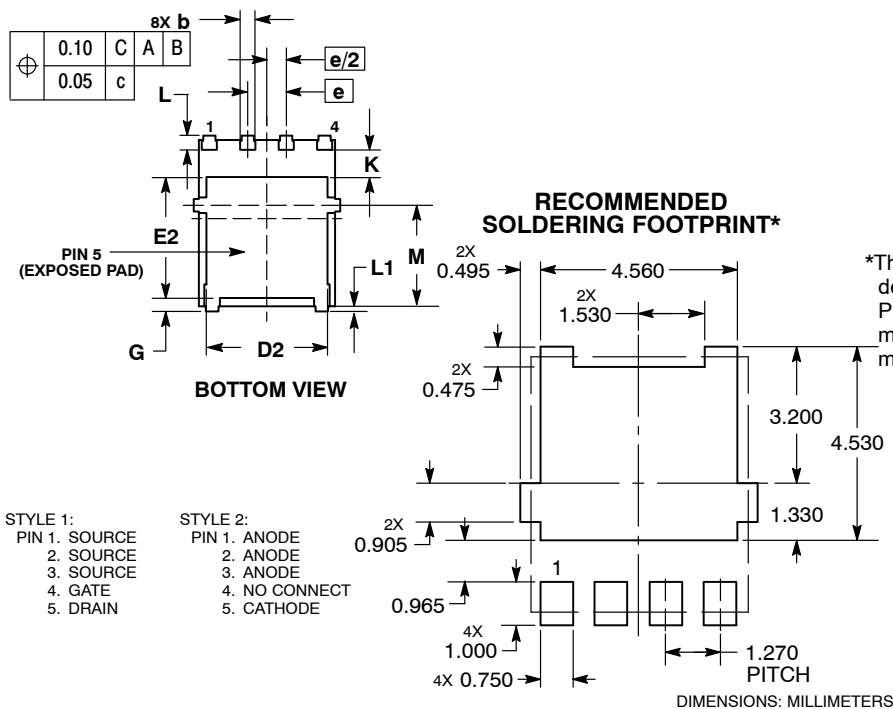
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

**GENERIC**  
**MARKING DIAGRAM\***


XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

STYLE 2:  
PIN 1. ANODE  
2. ANODE  
3. ANODE  
4. NO CONNECT  
5. CATHODE

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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<b>DESCRIPTION:</b>	<b>DFN5 5x6, 1.27P (SO-8FL)</b>	<b>PAGE 1 OF 1</b>

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